

	Type	L #	Hits	Search Text	DBs
1	BRS	L1	129949	438/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
2	BRS	L2	36679	1 and (MOS or transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
3	BRS	L3	24353	2 and (mask\$3 or photoresist)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
4	BRS	L4	7510	3 and (silicide or salicide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
5	BRS	L5	968	4 and (remov\$3 or etch\$3) near metal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
6	BRS	L6	235	5 and (sheet near resistance)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
7	BRS	L7	39	5 and (sheet near resistance) near (silicide or salicide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
8	BRS	L8	0	7 and (resistance near thickness)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
9	BRS	L9	3	6 and (resistance near thickness)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
10	BRS	L10	4	Gadepally-Kamesh-V.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
11	BRS	L11	8644	(silicide or salicide).ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
12	BRS	L12	619	11 and (sheet near resistance)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
13	BRS	L13	4	12 and (resistance near thickness)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
14	BRS	L14	538283	(MOS or transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
15	BRS	L15	68814	14 and (mask\$3 or photoresist)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
16	BRS	L16	3417	15 and (remov\$3 or etch\$3) near metal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
17	BRS	L17	49	16 and (sheet near resistance) near (silicide or salicide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB